Central™
Semiconductor Corp.

PROCESS CPD80

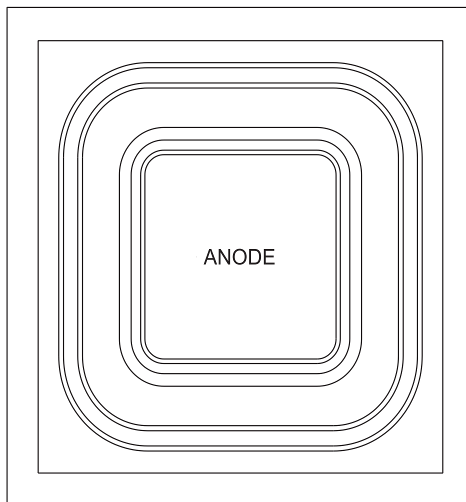
Switch Diode

High Voltage Switching Diode Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	16 x 16 MILS
Die Thickness	9.0 MILS
Anode Bonding Pad Area	6.5 x 6.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE CATHODE

GROSS DIE PER 4 INCH WAFER
45,050

PRINCIPAL DEVICE TYPES
CMPD2003
CMPD2004
1N3070
CMDD2003
CMDD2004

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

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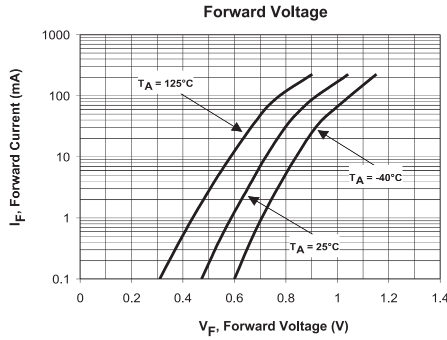
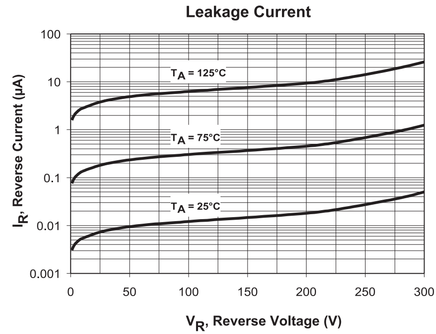
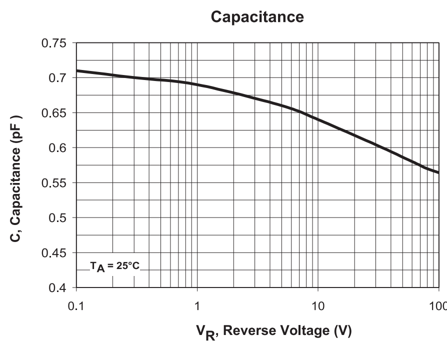
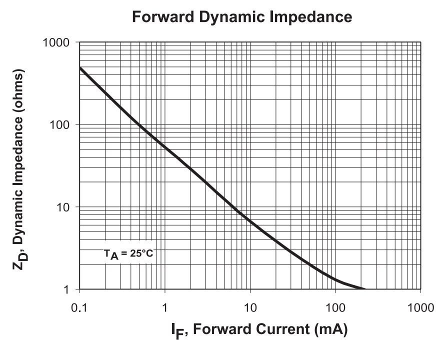
PROCESS CPD80

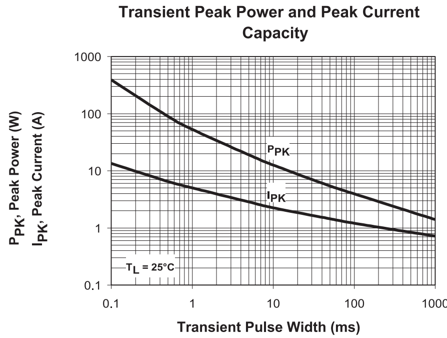
Typical Electrical Characteristics

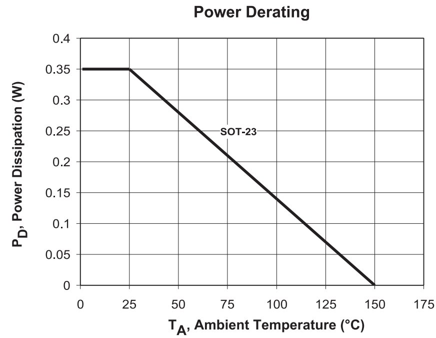












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